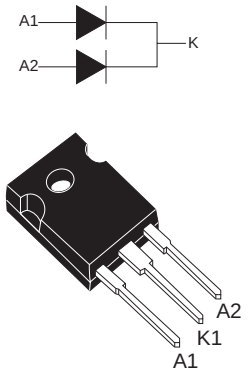
STPS40H100CW

HIGH VOLTAGE POWER SCHOTTKY RECTIFIER

MAIN PRODUCT CHARACTERISTICS

$I_{F(AV)}$	2 x 20 A
V_{RRM}	100 V
Tj (max)	175 °C
V_F (max)	0.61 V



TO-247

FEATURES AND BENEFITS

- NEGLIGIBLE SWITCHING LOSSES
- LOW LEAKAGE CURRENT
- GOOD TRADE OFF BETWEEN LEAKAGE CURRENT AND FORWARD VOLTAGE DROP
- LOW THERMAL RESISTANCE
- AVALANCHE CAPABILITY SPECIFIED

DESCRIPTION

Dual center tap Schottky rectifier suited for Switch Mode Power Supplies and high frequency DC to DC converters.

Packaged in TO-247, this device is intended for use in high frequency inverters.

ABSOLUTE RATINGS (limiting values, per diode)

Symbol	Parameter			Value	Unit
V_{RRM}	Repetitive peak reverse voltage			100	V
$I_{F(RMS)}$	RMS forward current			30	A
$I_{F(AV)}$	Average forward current	Tc = 160°C δ = 0.5	Per diode Per device	20 40	A
I_{FSM}	Surge non repetitive forward current	tp = 10 ms sinusoidal		300	A
I_{RRM}	Repetitive peak reverse current	tp = 2 µs F = 1kHz square		1	A
I_{RSM}	Non repetitive peak reverse current	tp = 100 µs square		4	A
E_{AS}	Non repetitive avalanche energy	Tj = 25°C L= 60 mH I_{as} = 3 A		36	mJ
P_{ARM}	Repetitive peak avalanche power	tp = 1µs Tj = 25°C		26400	W
T_{stg}	Storage temperature range			- 65 to + 175	°C
Tj	Maximum operating junction temperature			175	°C
dV/dt	Critical rate of rise of rise voltage			10000	V/µs

This datasheet has been downloaded from http://www.digchip.com at this page

THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th\ (j-c)}$	Junction to case	Per diode Total	0.9 0.55	°C/W
$R_{th\ (c)}$		Coupling	0.1	

When the diodes 1 and 2 are used simultaneously :
Δ Tj(diode 1) = P(diode1) x $R_{th(j-c)}$(Per diode) + P(diode 2) x $R_{th(c)}$

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Tests Conditions		Min.	Typ.	Max.	Unit
I_R *	Reverse leakage current	Tj = 25°C	$V_R = V_{RRM}$			10	µA
		Tj = 125°C			5	15	mA
V_F **	Forward voltage drop	Tj = 25°C	I_F = 20 A			0.73	V
		Tj = 125°C	I_F = 20 A		0.58	0.61	
		Tj = 25°C	I_F = 40 A			0.85	
		Tj = 125°C	I_F = 40 A		0.67	0.72	

Pulse test : * tp = 5 ms, δ < 2%
** tp = 380 µs, δ < 2%

To evaluate the maximum conduction losses use the following equation :
P = 0.5 x $I_{F(AV)}$ + 0.0055 x $I_F^2{}_{(RMS)}$

Fig. 1: Average forward power dissipation versus average forward current (per diode).

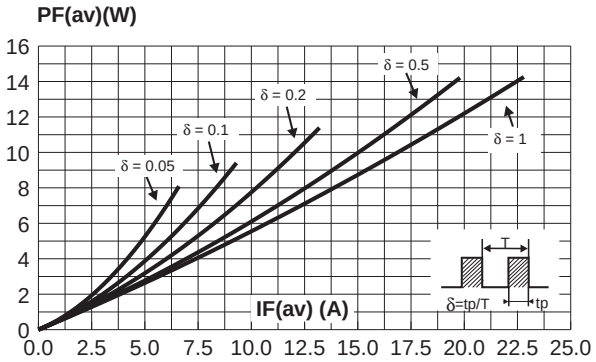


Fig. 2: Average forward current versus ambient temperature (δ=0.5, per diode).

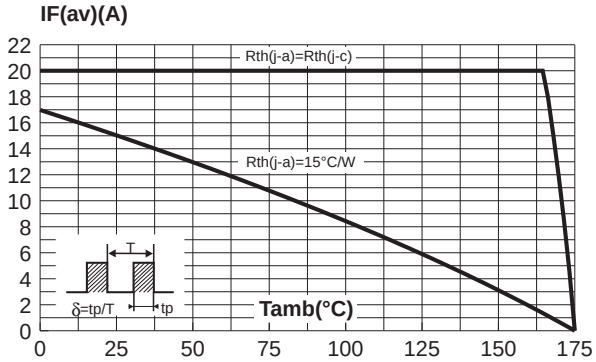


Fig. 3: Normalized avalanche power derating versus pulse duration.

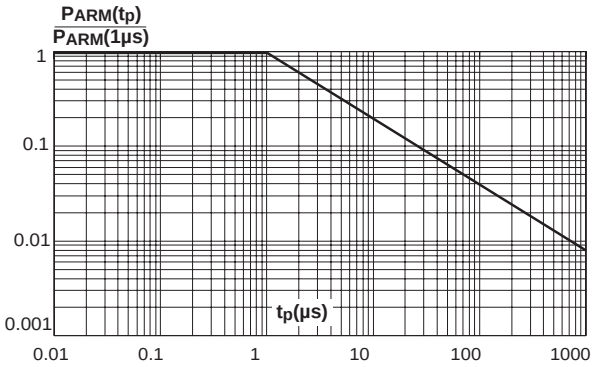


Fig. 4: Normalized avalanche power derating versus junction temperature.

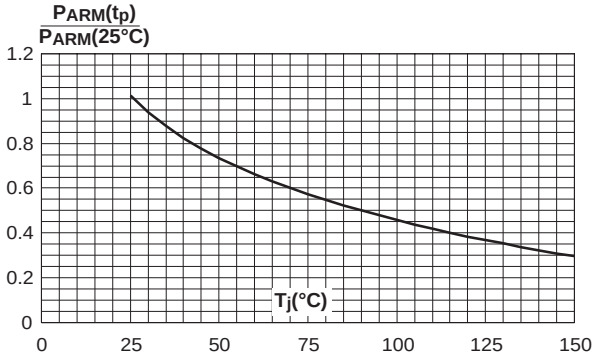


Fig. 5: Non repetitive surge peak forward current versus overload duration (maximum values, per diode).

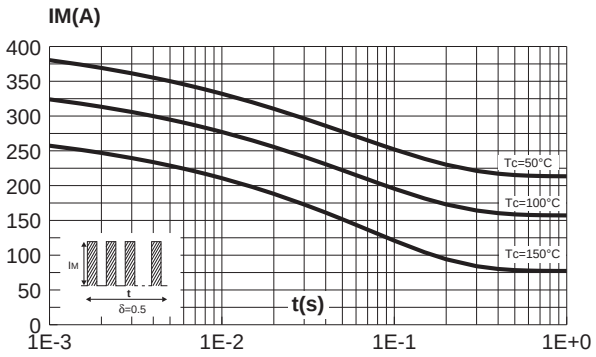


Fig. 6: Relative variation of thermal impedance junction to case versus pulse duration.

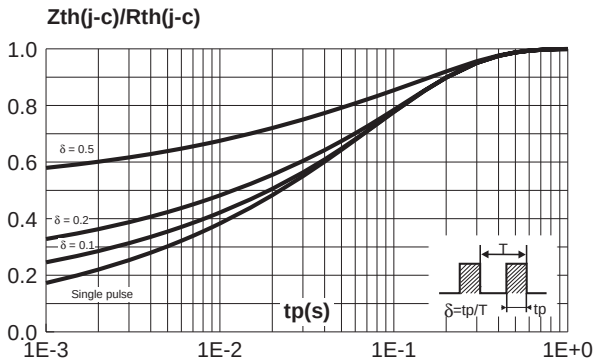


Fig. 7: Reverse leakage current versus reverse voltage applied (maximum values, per diode).

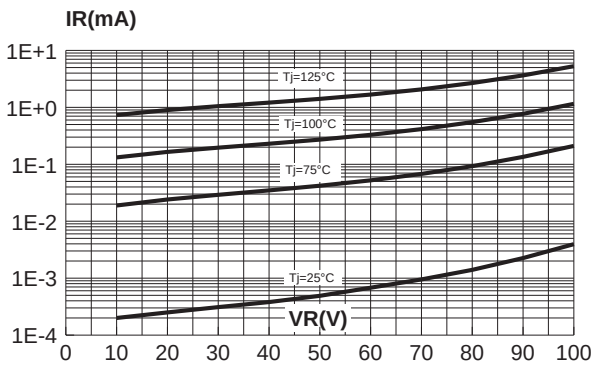


Fig. 8: Junction capacitance versus reverse voltage applied (typical values, per diode).

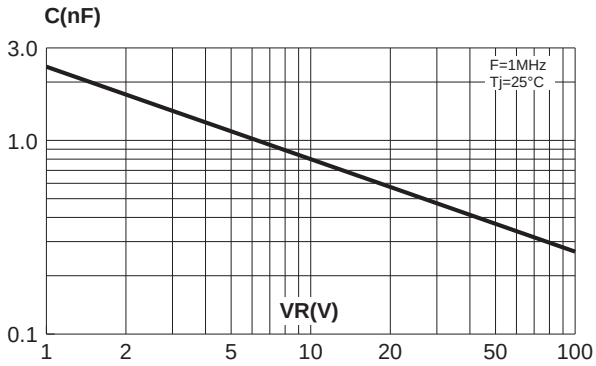
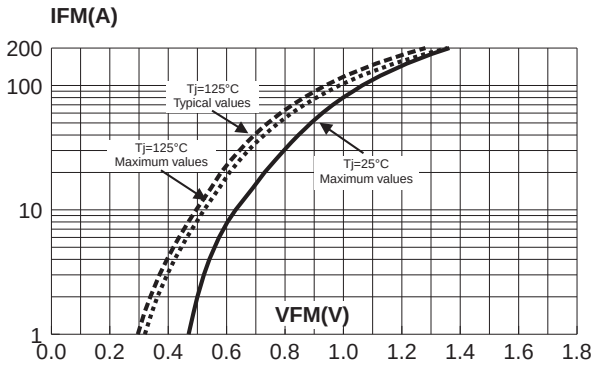
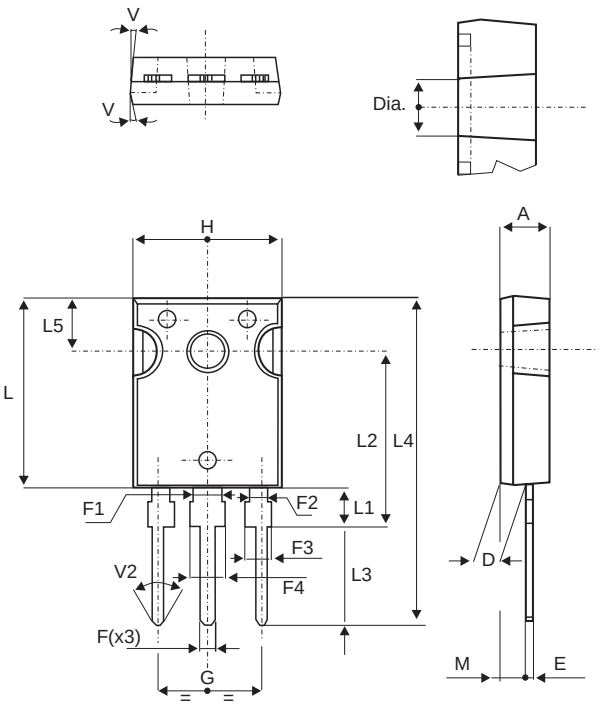


Fig. 9: Forward voltage drop versus forward current (per diode).



PACKAGE MECHANICAL DATA
TO-247



REF.	DIMENSIONS					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.85		5.15	0.191		0.203
D	2.20		2.60	0.086		0.102
E	0.40		0.80	0.015		0.031
F	1.00		1.40	0.039		0.055
F1		3.00			0.118	
F2		2.00			0.078	
F3	2.00		2.40	0.078		0.094
F4	3.00		3.40	0.118		0.133
G		10.90			0.429	
H	15.45		15.75	0.608		0.620
L	19.85		20.15	0.781		0.793
L1	3.70		4.30	0.145		0.169
L2		18.50			0.728	
L3	14.20		14.80	0.559		0.582
L4		34.60			1.362	
L5		5.50			0.216	
M	2.00		3.00	0.078		0.118
V		5°			5°	
V2		60°			60°	
Dia.	3.55		3.65	0.139		0.143

- Cooling method: C
- Recommended torque value: 0.8 N.m.
- Maximum torque value: 1 N.m.

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STPS40H100CW	STPS40H100CW	TO-247	4.36g	30	Tube

- Epoxy meets UL94,V0

Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied.
STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is a registered trademark of STMicroelectronics

© 2003 STMicroelectronics - Printed in Italy - All rights reserved.

STMicroelectronics GROUP OF COMPANIES
Australia - Brazil - Canada - China - Finland - France - Germany
Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Singapore
Spain - Sweden - Switzerland - United Kingdom - United States.

http://www.st.com